

Amendments to the Claims

This listing of claims will replace all prior versions and listings of claims in the application:

Listing of Claims

Claims 1-4 (**Canceled**).

Claim 5 (**Currently Amended**): ~~The method of claim 1,~~ A method for clamping a reticle within a lithography system, comprising:

clamping a first area of the reticle to a chuck of the lithography system at a first time point;

clamping a second area of the reticle to the chuck at a second time point after the first time point such that the reticle is flattened against the chuck;

wherein the chuck is an electrostatic chuck having a first pair of electrodes and a second pair of electrodes, ~~and wherein the method further comprises:~~

applying a voltage difference across the first pair of electrodes facing a first coating at the first area of the reticle at the first time point for clamping the first area to the chuck; and

applying a voltage difference across the second pair of electrodes facing a second coating at the second area of the reticle at the second time point for clamping the second area to the chuck.

Claim 6 (**Currently Amended**): The method of claim ~~[[1]]~~ 5, wherein the lithography system uses extreme ultraviolet light having a wavelength in a range of from about 110Å to about 150Å.

Claim 7 (**Currently Amended**): The method of claim ~~[[1]]~~ 5, wherein light reflected from the reticle is used for patterning material on a semiconductor wafer within the lithography system.

Claims 8-11 (**Canceled**).

Claim 12 (**Currently Amended**): ~~The system of claim 8,~~ A system for clamping a reticle within a lithography system, comprising:

means for clamping a first area of the reticle to a chuck of the lithography system at a first time point;

means for clamping a second area of the reticle to the chuck at a second time point after the first time point such that the reticle is flattened against the chuck;

wherein the chuck is an electrostatic chuck having a first pair of electrodes and a second pair of electrodes, ~~the system further comprising:~~

means for applying a voltage difference across the first pair of electrodes facing a first coating at the first area of the reticle at the first time point for clamping the first area to the chuck; and

means for applying a voltage difference across the second pair of electrodes facing a second coating at the second area of the reticle at the second time point for clamping the second area to the chuck.

Claim 13 (**Currently Amended**): The system of claim ~~[[8]]~~ 12, wherein the lithography system uses extreme ultraviolet light having a wavelength in a range of from about 110Å to about 150Å.

Claim 14 (**Currently Amended**): The system of claim ~~[[8]]~~ 12, wherein light reflected from the reticle is used for patterning material on a semiconductor wafer within the lithography system.

Claim 15 (**Original**): A lithography system comprising:

an electrostatic chuck having a first pair of electrodes and a second pair of electrodes;

a reticle having a first coating and a second coating facing the chuck;

a voltage source; and

a data processor that controls the voltage source to apply a voltage difference across the

first pair of electrodes facing the first coating at a first area of the reticle at a first time point for clamping the first area to the chuck, and that controls the voltage source to apply a voltage difference across the second pair of electrodes facing the second coating at a second area of the reticle at a second time point for clamping the second area to the chuck, such that the reticle is flattened against the chuck.

Claim 16 (**Original**): The lithography system of claim 15, wherein the first area is toward a center of the reticle, and wherein the second area is toward an outer perimeter of the reticle.

Claim 17 (**Original**): The lithography system of claim 15, wherein the reticle has a square shape, and wherein the first area is disposed at a center of the reticle, and wherein the second area is a frame disposed toward an outer perimeter of the reticle.

Claim 18 (**Original**): The lithography system of claim 15, wherein the lithography system uses extreme ultraviolet light having a wavelength in a range of from about 110Å to about 150Å.

Claim 19 (**Original**): The lithography system of claim 15, wherein light reflected from the reticle is used for patterning material on a semiconductor wafer within the lithography system.

Claim 20 (**New**): The method of claim 5, wherein the first area is toward a center of the reticle, and wherein the second area is toward an outer perimeter of the reticle.

Claim 21 (**New**): The method of claim 5, wherein the reticle has a square shape, and wherein the first area is disposed at a center of the reticle, and wherein the second area is a frame disposed toward an outer perimeter of the reticle.

Claim 22 (New): The method of claim 5, wherein the first area is at a center of the reticle that has a square shape, and wherein the method further comprises:

clamping each of a plurality of frames of the reticle to the chuck successively in time from the center toward an outer perimeter of the reticle.

Claim 23 (New): The system of claim 12, wherein the first area is toward a center of the reticle, and wherein the second area is toward an outer perimeter of the reticle.

Claim 24 (New): The system of claim 12, wherein the reticle has a square shape, and wherein the first area is disposed at a center of the reticle, and wherein the second area is a frame disposed toward an outer perimeter of the reticle.

Claim 25 (New): The system of claim 12, wherein the first area is at a center of the reticle that has a square shape, the system further comprising:

means for clamping each of a plurality of frames of the reticle to the chuck successively in time from the center toward an outer perimeter of the reticle.